Karen L Kavanagh

List of Publications by Year
in descending order

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		81900	54911
203	7,570	39	84
papers	citations	h-index	g-index

206	206	206	6592
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Rotational epitaxy of h-BNÂon Cu (110). Surface Science, 2022, 721, 122080.	1.9	3
2	Three-Dimensional Conductive Fingerprint Phantoms Made of Ethylene-Vinyl Acetate/Graphene Nanocomposite for Evaluating Smartphone Scanners. ACS Applied Electronic Materials, 2021, 3, 2097-2105.	4.3	4
3	Geometric effects on carrier collection in coreâ€“shell nanowire pâ€“n junctions. Nano Futures, 2021, 5, 025007.	2.2	1
4	Abrupt degenerately-doped silicon nanowire tunnel junctions. Nanotechnology, 2020, 31, 415708.	2.6	2
5	Understanding gaas Native Oxides By Correlating Three Liquid Contact Angle Analysis (3LCAA) and High Resolution Ion Beam Analysis (HR-IBA) to X-Ray Photoelectron Spectroscopy (XPS) as Function of Surface Processing. MRS Advances, 2019, 4, 2249-2263.	0.9	1
6	Three-Dimensional Imaging of Beam-Induced Biasing of InP/GaInP Tunnel Diodes. Nano Letters, 2019, 19, 3490-3497.	9.1	4
7	Axial EBIC oscillations at core/shell GaAs/Fe nanowire contacts. Nanotechnology, 2019, 30, 025701.	2.6	4
8	Role of Hydrogen Evolution during Epitaxial Electrodeposition of Fe on GaAs. Journal of the Electrochemical Society, 2018, 165, H3076-H3079.	2.9	10
9	Growth of h-BN on copper (110) in a LEEM. Surface Science, 2018, 669, 133-139.	1.9	10
10	Electrical characterization of Si/InN nanowire heterojunctions. Semiconductor Science and Technology, 2018, 33, 015008.	2.0	4
11	Measuring Surface Energies of GaAs (100) and Si (100) by Three Liquid Contact Angle Analysis (3LCAA) for Heterogeneous Nano-BondingTM. MRS Advances, 2018, 3, 3403-3411.	0.9	3
12	Aligned cuboid iron nanoparticles by epitaxial electrodeposition. Nanoscale, 2017, 9, 5315-5322.	5.6	8
13	Space-charge-limited current in nanowires. Journal of Applied Physics, 2017, 121, .	2.5	24
14	Electrical properties of lightly Ga-doped ZnO nanowires. Semiconductor Science and Technology, 2017, 32, 125010.	2.0	8
15	Regrowth mechanism for oxide isolation of GaAs nanowires. Nanotechnology, 2017, 28, 385302.	2.6	3
16	Interfacial reactions at Fe/topological insulator spin contacts. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2017, 35, 04F105.	1.2	6
17	Magnetic phase shift reconstruction for uniformly magnetized nanowires. Ultramicroscopy, 2017, 172, 10-16.	1.9	0
18	Direct Measurement of the Electrical Abruptness of a Nanowire pâ€“n Junction. Nano Letters, 2016, 16, 3982-3988.	9.1	23

#	Article	IF	Citations
19	Lithography-Free Fabrication of Coreâ€“Shell GaAs Nanowire Tunnel Diodes. Nano Letters, 2015, 15, 5408-5413.	9.1	14
20	Nanocontacts. Semiconductor Science and Technology, 2014, 29, 050301.	2.0	0
21	Hanle measurements of electrodeposited Fe/GaAs spin tunnel contacts. Journal of Applied Physics, 2014, 115, 123709.	2.5	2
22	Optical response of large-area aluminum-coated nano-bucket arrays on flexible PET substrates. Proceedings of SPIE, 2014, , .	0.8	0
23	Molecular beam epitaxial growth and characterization of intrinsic and p-type InN nanowires. Proceedings of SPIE, 2014, , .	0.8	0
24	Recycling gold nanohole arrays. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2014, 32, .	2.1	6
25	Characterization of solution-bonded GaAs/InGaAs/GaAs features on GaAs. Semiconductor Science and Technology, 2014, 29, 075009.	2.0	3
26	Magnetic Characterization of Isolated CoFeB/Cu Nanowires by Off-Axis Electron Holography. Microscopy and Microanalysis, 2014, 20, 280-281.	0.4	0
27	Large-Area Low-Cost Flexible Plastic Nanohole Arrays for Integrated Bio-Chemical Sensing. IEEE Sensors Journal, 2013, 13, 3982-3990.	4.7	15
28	Improved chemical and electrical stability of gold silicon contacts via epitaxial electrodeposition. Journal of Applied Physics, 2013, 113, 063708.	2.5	5
29	Direct Measurement of Coherency Limits for Strain Relaxation in Heteroepitaxial Core/Shell Nanowires. Nano Letters, 2013, 13, 1869-1876.	9.1	80
30	Lateral spin injection and detection through electrodeposited Fe/GaAs contacts. Semiconductor Science and Technology, 2013, 28, 035003.	2.0	7
31	Growth and strain relaxation of GaAs and GaP nanowires with GaSb shells. Journal of Applied Physics, 2013, 113, 134309.	2.5	22
32	Probing the electrical transport properties of intrinsic InN nanowires. Applied Physics Letters, 2013, 102, .	3.3	48
33	Geometric limits of coherent III-V core/shell nanowires. Journal of Applied Physics, 2013, 114, .	2.5	39
34	Metastable phase formation in the Au-Si system via ultrafast nanocalorimetry. Journal of Applied Physics, 2012, 111, .	2.5	24
35	p-type doping of GaAs nanowires using carbon. Journal of Applied Physics, 2012, 112, 094323.	2.5	14
36	Controlled axial and radial Te-doping of GaAs nanowires. Journal of Applied Physics, 2012, 112, 054324.	2.5	12

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37	Insights into semiconductor nanowire conductivity using electrodeposition. Semiconductor Science and Technology, 2012, 27, 105020.	2.0	2
38	Reduction of Gold Penetration through Phenyl-Terminated Alkyl Monolayers on Silicon. Journal of Physical Chemistry C, 2012, 116, 17040-17047.	3.1	25
39	Epitaxial Growth of Metals on Semiconductors Via Electrodeposition. , 2012, , 217-235.		1
40	Faster radial strain relaxation in InAsâ€“GaAs coreâ€“shell heterowires. Journal of Applied Physics, 2012, 111, .	2.5	57
41	Detecting Antibodies Secreted by Trapped Cells Using Extraordinary Optical Transmission. IEEE Sensors Journal, 2011, 11, 2732-2739.	4.7	9
42	Preparation of ideal molecular junctions: depositing non-invasive gold contacts on molecularly modified silicon. Nanoscale, 2011, 3, 1434.	5.6	23
43	Electrodeposition, characterization and morphological investigations of NiFe/Cu multilayers prepared by pulsed galvanostatic, dual bath technique. Materials Characterization, 2011, 62, 204-210.	4.4	12
44	Improved Performance of Nanohole Surface Plasmon Resonance Sensors by the Integrated Response Method. IEEE Photonics Journal, 2011, 3, 441-449.	2.0	25
45	Long-lasting flexible organic solar cells stored and tested entirely in air. Applied Physics Letters, 2011, 99, 263305.	3.3	10
46	Transport and strain relaxation in wurtzite InAsâ€“GaAs core-shell heterowires. Applied Physics Letters, 2011, 98, .	3.3	57
47	Rectifying characteristics of Te-doped GaAs nanowires. Applied Physics Letters, 2011, 99, 182102.	3.3	29
48	Title is missing!. Journal of Medical and Biological Engineering, 2011, 31, 121.	1.8	5
49	Misfit dislocations in nanowire heterostructures. Semiconductor Science and Technology, 2010, 25, 024006.	2.0	149
50	Resonant optical transmission through holeâ€arrays in metal films: physics and applications. Laser and Photonics Reviews, 2010, 4, 311-335.	8.7	150
51	Sensing of antibodies secreted by microfluidically trapped cells via extraordinary optical transmission through nanohole arrays. , 2010, , .		4
52	Effect of annealing on the structural and optical properties of heavily carbon-doped ZnO. Semiconductor Science and Technology, 2010, 25, 045023.	2.0	4
53	A New Technique for Magnetic Nanoparticle Imaging Using Magnetoencephalography Frequency Data. IFMBE Proceedings, 2010, , 443-446.	0.3	3
54	Residual Stress, Defects, and Electrical Properties of Epitaxial Copper Growth on GaAs. Journal of the Electrochemical Society, 2009, 156, D138.	2.9	12

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55	Inhomogeneous magnetization processes in electrodeposited iron thin films on GaAs. Journal of Applied Physics, 2009, 105, .	2.5	2
56	Structural and Roomâ€Temperature Transport Properties of Zinc Blende and Wurtzite InAs Nanowires. Advanced Functional Materials, 2009, 19, 2102-2108.	14.9	86
57	Growth of InAsSb/InAs MQWs on GaSb for mid-IR photodetector applications. Journal of Crystal Growth, 2009, 311, 3563-3567.	1.5	31
58	Atomic ordering in GaAsSb (001) grown by metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2009, 311, 4391-4397.	1.5	6
59	Molecular Orientation in Octanedithiol and Hexadecanethiol Monolayers on GaAs and Au Measured by Infrared Spectroscopic Ellipsometry. Langmuir, 2009, 25, 919-923.	3.5	37
60	Structural and electrical characteristics of nanocrystalline silicon prepared by hot-wire chemical vapor deposition on polymer substrates. Thin Solid Films, 2008, 516, 7418-7421.	1.8	1
61	Field Dependent Transport Properties in InAs Nanowire Field Effect Transistors. Nano Letters, 2008, 8, 3114-3119.	9.1	33
62	Nanoscale Electrical and Structural Characterization of Gold/Alkyl Monolayer/Silicon Diode Junctions. Journal of Physical Chemistry C, 2008, 112, 9081-9088.	3.1	39
63	A New Generation of Sensors Based on Extraordinary Optical Transmission. Accounts of Chemical Research, 2008, 41, 1049-1057.	15.6	492
64	Heteroepitaxial Growth of Vertical GaAs Nanowires on Si (111) Substrates by Metalâ^'Organic Chemical Vapor Deposition. Nano Letters, 2008, 8, 3755-3760.	9.1	93
65	Plasmonic sensors based on nano-holes: technology and integration. Proceedings of SPIE, 2008, , .	0.8	8
66	SU-8 polymer enclosed microchannels with interconnect and nanohole arrays as an optical detection device for biospecies. , 2008, 2008, 5652-5.		2
67	Epitaxial Fe[sub x]Ni[sub 1â^'x] Thin Film Contacts to GaAs via Electrochemistry. Journal of the Electrochemical Society, 2008, 155, H841.	2.9	9
68	Defect studies of ZnSe nanowires. Nanotechnology, 2008, 19, 215715.	2.6	36
69	Au â^• Ag and Auâ^•Pd molecular contacts to GaAs. Journal of Vacuum Science & Technology B, 2008, 26, 1597-1601.	1.3	6
70	Optimal Control over the InAs Nanowire Growth for System Integration and their Structural and Transport Properties. , 2008, , .		0
71	Nanoholes in metals with applications to sensors and spectroscopy. International Journal of Nanotechnology, 2008, 5, 1058.	0.2	4
72	Twinning modulation in ZnSe nanowires. Semiconductor Science and Technology, 2007, 22, 175-178.	2.0	37

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73	Structural and electrical characteristics of microcrystalline silicon prepared by hot-wire chemical vapor deposition using a graphite filament. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2007, 25, 464-467.	2.1	5
74	Structural Analysis of Nanocrystalline Silicon Prepared by Hot-wire Chemical Vapor Deposition on Polymer Substrates. Materials Research Society Symposia Proceedings, 2007, 989, 3.	0.1	1
75	Double nanohole-enhanced Raman spectroscopy. , 2007, , .		0
76	Ballistic electron and photocurrent transport in Au-molecular layer-GaAs diodes. Journal of Applied Physics, 2007, 102, .	2.5	11
77	Double nanohole-enhanced Raman spectroscopy. , 2007, , .		0
78	Structure and photoluminescence of ZnSe nanostructures fabricated by vapor phase growth. Journal of Applied Physics, 2007, 101, 014326.	2.5	38
79	Transparent conducting indium bismuth oxide. Thin Solid Films, 2007, 515, 3760-3765.	1.8	5
80	Apex-Enhanced Raman Spectroscopy Using Double-Hole Arrays in a Gold Film. Journal of Physical Chemistry C, 2007, 111, 2347-2350.	3.1	96
81	Enhancement of band edge luminescence in ZnSe nanowires. Journal of Applied Physics, 2006, 100, 084316.	2.5	78
82	Surface Plasmonâ˜'Quantum Dot Coupling from Arrays of Nanoholes. Journal of Physical Chemistry B, 2006, 110, 8307-8313.	2.6	64
83	Microstructure of ordered nanodomains induced by Bi surfactant in OMVPE-grown GaAsSb. Journal of Crystal Growth, 2006, 287, 541-544.	1.5	3
84	Aligned Co nanodiscs by electrodeposition on GaAs. Journal of Crystal Growth, 2006, 287, 514-517.	1.5	24
85	Planar defects and phase transformation in ZnSe nanosaws. Journal of Materials Science: Materials in Electronics, 2006, 17, 1065-1070.	2.2	9
86	Developing 1D nanostructure arrays for future nanophotonics. Nanoscale Research Letters, 2006, 1, 99-119.	5.7	46
87	Epitaxial Biâ•GaAs diodes via electrodeposition. Journal of Vacuum Science & Technology B, 2006, 24, 2138.	1.3	19
88	Light induced degradation in amorphous silicon photodiodes and implication for diagnostic medical imaging application. , 2006, 6142, 967.		1
89	Effects of HWCVD-deposited Seed Layers on Hydrogenated Microcrystalline Silicon Films on Glass Substrates. Materials Research Society Symposia Proceedings, 2006, 910, 5.	0.1	1
90	Epitaxial Biâ•GaAs(111) diodes via electrodeposition. Applied Physics Letters, 2006, 88, 022102.	3.3	17

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91	Enhanced Fluorescence from Arrays of Nanoholes in a Gold Film. Journal of the American Chemical Society, 2005, 127, 14936-14941.	13.7	203
92	Strain relaxation by ã€ˆ100ã€‰ misfit dislocations in dilute nitride InxGa1-xAs1-yNy/GaAs quantum wells. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 2849-2857.	1.8	7
93	Temporary extrusion failures in accelerated lifetime tests of copper interconnects. IEEE Electron Device Letters, 2005, 26, 622-624.	3.9	2
94	Characterization of Temporary Extrusion Failures in Quarter-Micron Copper Interconnects. Materials Research Society Symposia Proceedings, 2005, 863, B9.7-1.	0.1	0
95	Structural and magnetic properties of NiMnSb/InGaAs/InP(001). Journal of Applied Physics, 2005, 97, 073906.	2.5	19
96	Ballistic Electron Emission Microscopy Studies of Au/Molecule/n-GaAs Diodes. Journal of Physical Chemistry B, 2005, 109, 6252-6256.	2.6	33
97	Basis and Lattice Polarization Mechanisms for Light Transmission through Nanohole Arrays in a Metal Film. Nano Letters, 2005, 5, 1243-1246.	9.1	66
98	Epitaxial Feâ•GaAs via electrochemistry. Journal of Applied Physics, 2005, 98, 066103.	2.5	22
99	Electrokinetically-Induced Flow Over a Nano-Hole Array Sensor. , 2004, , 213.		1
100	Effects of capillary forces on copperâ•dielectric interfacial void evolution. Applied Physics Letters, 2004, 84, 5201-5203.	3.3	9
101	Effect of Bi surfactant on atomic ordering of GaAsSb. Applied Physics Letters, 2004, 85, 5589-5591.	3.3	10
102	Strong Polarization in the Optical Transmission through Elliptical Nanohole Arrays. Physical Review Letters, 2004, 92, 037401.	7.8	439
103	Evolution of interface voids under current and temperature stress in integrated circuit metallization. Metals and Materials International, 2004, 10, 411-415.	3.4	4
104	Surface Plasmon Sensor Based on the Enhanced Light Transmission through Arrays of Nanoholes in Gold Films. Langmuir, 2004, 20, 4813-4815.	3.5	715
105	Nanohole-Enhanced Raman Scattering. Nano Letters, 2004, 4, 2015-2018.	9.1	418
106	Antimony segregation in GaAs-based multiple quantum well structures. Journal of Crystal Growth, 2003, 254, 28-34.	1.5	23
107	Substrate effects on the ferroelectric properties of fine-grained BaTiO3 films. Journal of Applied Physics, 2003, 94, 5982-5989.	2.5	26
108	Growth, branching, and kinking of molecular-beam epitaxial ã€ˆ110ã€‰ GaAs nanowires. Applied Physics Letters, 2003, 83, 3368-3370.	3.3	112

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109	Comparison of strain relaxation in InGaAsN and InGaAs thin films. Applied Physics Letters, 2002, 80, 4357-4359.	3.3	22
110	Scanning spreading resistance microscopy current transport studies on doped IIIâ€“V semiconductors. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 1682.	1.6	36
111	Wavelength-Invariant Resist Composed of Bimetallic Layers. Materials Research Society Symposia Proceedings, 2002, 745, 381.	0.1	8
112	Ballistic electron emission microscopy studies of ZnSeâ€“BeTe heterojunctions. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 1781.	1.6	0
113	Evolution of GaSb/GaAs Quantum Dot Strain Relaxation. Microscopy and Microanalysis, 2002, 8, 1200-1201.	0.4	0
114	The growth of SiGe on sapphire using rapid thermal chemical vapor deposition. Journal of Crystal Growth, 2001, 222, 20-28.	1.5	9
115	X-Ray Diffuse Scattering from Misfit Dislocation at Buried Interface. Materials Research Society Symposia Proceedings, 2001, 673, 1.	0.1	7
116	Faceting transition in epitaxial growth of dilute GaNAs films on GaAs. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 1417.	1.6	12
117	Calibrated scanning spreading resistance microscopy profiling of carriers in IIIâ€“V structures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 1662.	1.6	32
118	Anisotropic resistivity correlated with atomic ordering in p-type GaAsSb. Applied Physics Letters, 2001, 79, 2384-2386.	3.3	31
119	Gas-source molecular beam epitaxial growth and thermal annealing of GaInNAs/GaAs quantum wells. Journal of Crystal Growth, 2000, 208, 145-152.	1.5	38
120	Interfacial scattering of hot electrons in ultrathin Au/Co films. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 2047.	1.6	6
121	Hot-electron attenuation lengths in ultrathin magnetic films. Journal of Applied Physics, 2000, 87, 5164-5166.	2.5	23
122	Atomic interface structure-property investigations. Canadian Journal of Physics, 2000, 77, 985-994.	1.1	0
123	Atomic interface structure-property investigations. Canadian Journal of Physics, 2000, 78, 201-210.	1.1	1
124	Atomic interface structure-property investigations. Canadian Journal of Physics, 2000, 78, 201-210.	1.1	0
125	Quantum dot-like behavior of GaInNAs in GaInNAs/GaAs quantum wells grown by gas-source molecular-beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1649.	1.6	19
126	Suppression of growth-induced perpendicular magnetic anisotropy in Coâ€“Pt alloys by trace amounts of Si. Applied Physics Letters, 1999, 75, 4177-4179.	3.3	1

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127	Observation of quantum dot-like behavior of GaInNAs in GaInNAs/GaAs quantum wells. Applied Physics Letters, 1999, 74, 2337-2339.	3.3	126
128	Effects of rapid thermal annealing on GaInNAs/GaAs multiple quantum wells. Journal of Crystal Growth, 1999, 201-202, 419-422.	1.5	78
129	Growth-induced magnetic anisotropy and clustering in vapor-deposited Co-Pt alloy films. Physical Review B, 1999, 60, 12826-12836.	3.2	49
130	Hole confinement and low-frequency noise in SiGe pFETs on silicon-on-sapphire. IEEE Electron Device Letters, 1999, 20, 173-175.	3.9	9
131	Effects of GaAs substrate misorientation on strain relaxation in InxGa1â^'xAs films and multilayers. Journal of Applied Physics, 1998, 83, 5137-5149.	2.5	102
132	Effect of Oxygen on the Degradation of Ti-Si-N Diffusion Barriers in Cu Metallization. Materials Research Society Symposia Proceedings, 1998, 514, 321.	0.1	1
133	Analysis Of Sige Fet Device Structures On Silicon-on-sapphire Substrates by X-Ray Diffraction. Materials Research Society Symposia Proceedings, 1998, 533, 55.	0.1	2
134	<title>In-situ measurement of roughness spectra using diffuse scattering</title>. , 1997, , .		1
135	Compositional Effects on the Degradation of PVD-Tisin. Materials Research Society Symposia Proceedings, 1997, 472, 325.	0.1	1
136	Compositional Effects on the Degradation of PVD-Tisin. Materials Research Society Symposia Proceedings, 1997, 473, 241.	0.1	0
137	Au/ZnSe contacts characterized by ballistic electron emission microscopy. Journal of Applied Physics, 1996, 79, 1532-1535.	2.5	15
138	A Study of Low-Temperature Grown Gap by Gas-Source Molecular Beam Epitaxy. Materials Research Society Symposia Proceedings, 1996, 421, 293.	0.1	0
139	Correlation of buffer strain relaxation modes with transport properties of twoâ€dimensional electron gases. Journal of Applied Physics, 1996, 80, 6849-6854.	2.5	13
140	Comparison of Au contacts to Si, GaAs, InxGa1 â^' xP, and ZnSe measured by ballistic electron emission microscopy. Materials Chemistry and Physics, 1996, 46, 224-229.	4.0	8
141	Role of interface microstructure in rectifying metal/semiconductor contacts: Ballistic electron emission observations correlated to microstructure. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 1238.	1.6	15
142	Tensile strain relaxation in GaNxP1â^'x (xâ‰0.1) grown by chemical beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 2952.	1.6	11
143	Modulation-doped In0.53Ga0.47As/In0.52Al0.48As heterostructures grown on GaAs substrates using step-graded InxGa1â^'xAs buffers. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 3035.	1.6	8
144	Effects of Substrate Misorientation Direction on Strain Relaxation at InGaAs/GaAs(001) Interfaces. Materials Research Society Symposia Proceedings, 1995, 379, 21.	0.1	0

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145	Beem and UHV-TEM Studies of PtSi/Si(001). Materials Research Society Symposia Proceedings, 1995, 402, 461.	0.1	2
146	Structural and Electrical Characterization of Si-Implanted TiN as a Diffusion Barrier for Cu Metallization. Materials Research Society Symposia Proceedings, 1995, 391, 327.	0.1	1
147	Room-temperature electrosynthesis of carbonaceous fibers. Advanced Materials, 1995, 7, 398-401.	21.0	7
148	Relationship between surface morphology and strain relaxation during growth of InGaAs strained layers. Applied Physics Letters, 1995, 67, 3744-3746.	3.3	37
149	Study of Î¼mâ€scale spatial variations in strain of a compositionally stepâ€graded InxGa1âˆ'xAs/GaAs(001) heterostructure. Applied Physics Letters, 1995, 66, 869-871.	3.3	25
150	Relaxation-induced polarized luminescence fromInxGa1âˆ'xAs films grown on GaAs(001). Physical Review B, 1995, 51, 5033-5037.	3.2	14
151	Influence of GaAs(001) substrate misorientation towards {111} on the optical properties of InxGa1âˆ'xAs/GaAs. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 1766.	1.6	2
152	Correlation of anisotropic strain relaxation with substrate misorientation direction at InGaAs/GaAs(001) interfaces. Applied Physics Letters, 1995, 67, 344-346.	3.3	37
153	Homogeneous Strain Relaxation and Mosaic Spread in IngaAs/GaAs Heterostructures Using Triple Axis Diffractometry. , 1995, , 221-226.		2
154	Homogeneous Strain Relaxation and Mosaic Spread in InGaAs/GaAs Heterostructures Using Triple Axis Diffractometry. Advances in X-ray Analysis, 1994, 38, 221-226.	0.0	0
155	Nanometer-resolved spatial variations in the Schottky barrier height of a Au/n-type GaAs diode. Physical Review B, 1994, 49, 16474-16479.	3.2	45
156	Strain relaxation induced deep levels in In1âˆ'xGaxAs thin films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1994, 12, 1050-1053.	2.1	2
157	Optical detection of misfit dislocationâ€induced deep levels at InGaAs/GaAs heterojunctions. Applied Physics Letters, 1994, 64, 3572-3574.	3.3	15
158	Lateral variation in the Schottky barrier height of Au/PtSi/(100)Si diodes. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1994, 12, 2634.	1.6	26
159	Dislocation-Induced deep level states in In0.08Ga0.92As/GaAs heterostructures. Journal of Electronic Materials, 1994, 23, 929-933.	2.2	4
160	Anisotropic structural, electronic, and optical properties of InGaAs grown by molecular beam epitaxy on misoriented substrates. Applied Physics Letters, 1994, 65, 1424-1426.	3.3	22
161	Lateral Variation in the Schottky Barrier Height and Observation of Critical Lengths at Au/PtSi/(100)Si and Au/(100)GaAs Diodes. Materials Research Society Symposia Proceedings, 1994, 337, 319.	0.1	2
162	Anisotropic Structural and Electronic Properties of InGaAs/GaAs Heterojunctions. Materials Research Society Symposia Proceedings, 1994, 340, 349.	0.1	1

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163	The Effect of Starting Silicon Crystal Structure on Photoluminescence Intensity of Porous Silicon. Materials Research Society Symposia Proceedings, 1994, 358, 351.	0.1	1
164	Light Scattering Study of the Evolution of the Surface Morphology During Growth of Ingaas on GaAs. Materials Research Society Symposia Proceedings, 1994, 375, 193.	0.1	0
165	‹title›Control of surface morphology and strain relaxation in InGaAs grown on GaAs using a step-graded buffer‹/title›. , 1994, 2140, 179.		3
166	Si diffusion and segregation in lowâ€temperature grown GaAs. Applied Physics Letters, 1993, 62, 286-288.	3.3	8
167	Time dependent ballistic electron emission microscopy studies of a Au/(100)GaAs interface with a native oxide diffusion barrier. Applied Physics Letters, 1993, 62, 2965-2967.	3.3	30
168	Multiple dislocation loops in linearly graded InxGa1â^'xAs (0â‰xâ‰0.53) on GaAs and InxGa1â^'xP (0â‰xâ‰0.32) on GaP. Applied Physics Letters, 1993, 63, 500-502.	3.3	28
169	Gasâ€source molecular beam epitaxial growth, characterization, and lightâ€emitting diode application of InxGa1â^'xP on GaP(100). Applied Physics Letters, 1993, 62, 2369-2371.	3.3	29
170	Anisotropic Surface Roughness in Strain Relaxed In‹sub›0.40‹/sub›GA‹sub›0.60‹/sub›As on Gaas with a Step-Graded In‹sub›x‹/sub›GA‹sub›1-x‹/sub›As Buffer Layer. Materials Research Society Symposia Proceedings, 1993, 312, 107.	0.1	6
171	Modulation-doped In0.3Ga0.7As/In0.29Al0.71As heterostructures grown on GaAs by step grading. Semiconductor Science and Technology, 1992, 7, 601-603.	2.0	21
172	Oxidation induced AlAs/GaAs superlattice disordering. Applied Physics Letters, 1992, 60, 1235-1237.	3.3	4
173	Lattice tilt and dislocations in compositionally step-graded buffer layers for mismatched InGaAs/GaAs heterointerfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1992, 10, 1820.	1.6	49
174	Lattice strain from substitutional Ga and from holes in heavily doped Si:Ga. Physical Review B, 1992, 45, 3323-3331.	3.2	21
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